

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRA1417-6H** is a Common Base Device Designed for Class C Amplifier Applications in L-Band FM Microwave Links.

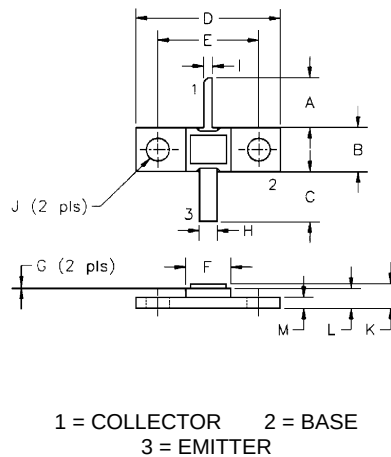
FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	1.0 A
V_{CBO}	50 V
P_{DISS}	19 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	9.0°C/W

PACKAGE STYLE .250 2L FLG (B)



DIM	MILLIMETER	TOL	INCHES	TOL
A	9.40	.61	.370	.024
B	6.60	.18	.250	.005
C	9.40	.61	.370	.024
D	20.32	.25	.800	.010
E	14.22	.13	.560	.005
F	6.35	.13	.250	.005
G	0.10	.05	.004	.002
H	2.54	.13	.100	.005
I	1.27	.13	.050	.005
J	3.30 DIA	.13	.130 DIA	.005
K	3.43	.13	.135	.005
L	2.79	.13	.110	.005
M	1.52	.13	.060	.005

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 25\text{ mA}$	50			V
BV_{CES}	$I_C = 25\text{ mA}$	55			V
BV_{EBO}	$I_E = 3.0\text{ mA}$	3.5			V
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	20		100	---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$		6.5		pF
P_G η_C	$V_{CE} = 28\text{ V}$ $P_{OUT} = 6.0\text{ W}$ $f = 1400 - 1700\text{ MHz}$	7.2	7.5 40		dB %